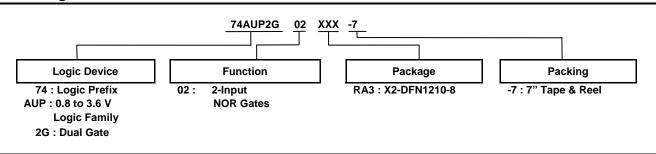


Ordering Information



	Package Package		Package	7" Tape and Reel		
Device	Code	(Notes 4 & 5)	Size	Quantity	Part Number Suffix	
74AUP2G02RA3-7	RA3	X2-DFN1210-8	1.2mm X 1.0mm X 0.35mm 0.3 mm lead pitch	5,000/Tape & Reel	-7	

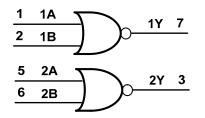
Notes: 4. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.

5. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Pin Descriptions

Pin Name	Pin No.	Function
1A	1	Data Input
1B	2	Data Input
2Y	3	Data Output
GND	4	Ground
2A	5	Data Input
2B	6	Data Input
1Y	7	Data Output
V _{CC}	8	Supply Voltage

Logic Diagram



Function Table

Inp	uts	Output
Α	В	Y
L	L	Н
L	Н	L
Н	L	L
Н	Н	L



Absolute Maximum Ratings (Notes 6 & 7)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	kV
ESD CDM	Charged Device Model ESD Protection	1	kV
ESD MM	Machine Model ESD Protection	200	V
V _{CC}	Supply Voltage Range	-0.5 to +4.6	V
VI	Input Voltage Range	-0.5 to +4.6	V
Vo	Voltage Applied to Output in High or Low State	-0.5 to V _{CC} +0.5	V
I _{IK}	Input Clamp Current VI<0	50	mA
Ι _{ΟΚ}	Output Clamp Current (V _O < 0)	50	mA
IO	Continuous Output Current ($V_0 = 0$ to V_{CC})	±20	mA
Icc	Continuous Current Through V _{CC}	50	mA
I _{GND}	Continuous Current Through GND	-50	mA
TJ	Operating Junction Temperature	-40 to +150	°C
T _{STG}	Storage Temperature	-65 to +150	°C

Notes: 6. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device

operation should be within recommend values.7. Forcing the maximum allowed voltage could cause a condition exceeding the maximum current or conversely forcing the maximum current could cause a condition exceeding the maximum voltage. The ratings of both current and voltage must be maintained within the controlled range.

Recommended Operating Conditions (Note 8)

Symbol	Pa	arameter	Min	Max	Unit
Vcc	Operating Voltage	_	0.8	3.6	V
VI	Input Voltage		0	3.6	V
Vo	Output Voltage		0	V _{CC}	V
		$V_{CC} = 0.8V$	—	-20	μA
		V _{CC} = 1.1V	—	-1.1	
	I _{OH} High-Level Output Current	$V_{CC} = 1.4V$	—	-1.7	
IOH		V _{CC} = 1.65V	—	-1.9	mA
		V _{CC} = 2.3V	—	-3.1	
		V _{CC} = 3.0V	—	-4	
		V _{CC} = 0.8V	—	20	μA
		V _{CC} = 1.1V	_	1.1	
		$V_{CC} = 1.4V$	_	1.7	
I _{OL}	Low-Level Output Current	V _{CC} = 1.65V	_	1.9	mA
		V _{CC} = 2.3V	_	3.1	
		V _{CC} = 3.0V	_	4	
Δt/ΔV	Input Transition Rise or Fall Rate	V _{CC} = 0.8V to 3.6V	—	200	ns/V
T _A	Operating Free-Air Temperature	_	-40	+125	°C

Note: 8. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics

Symbol	Baramatar	Test Conditions	V	T _A = -	+25°C	T _A = -40°0	C to +85°C	Unit
Symbol	Parameter	Test Conditions	V _{cc}	Min	Max	Min	Max	Unit
		_	0.8V to 1.65V	0.80 X V _{CC}	_	0.80 X V _{CC}	—	
N/	High-Level Input	-	1.65V to 1.95V	0.65 X V _{CC}	_	0.65 X V _{CC}	—	v
V _{IH}	Voltage	-	2.3V to 2.7V	1.6	_	1.6	—	V
		_	3.0V to 3.6V	2.0	—	2.0	—	
		—	0.8V to 1.65V	—	$0.30 \times V_{CC}$	—	$0.30 \times V_{CC}$	
VIL	Low-Level Input	l	1.65V to 1.95V	—	0.35 X V_{CC}	—	0.35 X V_{CC}	v
۷IL	Voltage	—	2.3V to 2.7V	—	0.7	—	0.7	v
			3.0V to 3.6V		0.9	_	0.9	
		I _{OH} = -20µА	0.8V to 3.6V	V _{CC} – 0.1	—	$V_{CC} - 0.1$	—	
		I _{OH} = -1.1mA	1.1V	0.75 X V_{CC}	—	0.7 X V _{CC}	—	
		I _{OH} = -1.7mA	1.4V	1.11	—	1.03	—	
	High-Level Output	I _{OH} = -1.9mA	1.65V	1.32	—	1.3	—	.,
Voh	Voltage	I _{OH} = -2.3mA	0.01/	2.05	_	1.97	—	V
		I _{OH} = -3.1mA	2.3V	1.9		1.85	—	
		I _{OH} = -2.7mA	o) /	2.72		2.67	_	
		I _{OH} = -4mA	- 3V	2.6	_	2.55	_	
		I _{OL} = 20μΑ	0.8V to 3.6V		0.1		0.1	
		I _{OL} = 1.1mA	1.1V	_	0.3 X V _{CC}	_	0.3 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.31	_	0.37	
	Low-Level Input	I _{OL} = 1.9mA	1.65V	_	0.31	_	0.35	
Vol	Voltage	I _{OL} = 2.3mA		_	0.31	_	0.33	V
		I _{OL} = 3.1mA	2.3V	_	0.44	—	0.45	
		I _{OL} = 2.7mA		_	0.31	_	0.33	
		I _{OL} = 4mA	3V	_	0.44	_	0.45	
I	Input Current	A or B Input VI = GND to 3.6V	0V to 3.6V	_	± 0.1	_	± 0.5	μΑ
I _{OFF}	Power Down Leakage Current	V_{I} or V_{O} = 0V to 3.6V	0V	_	± 0.2		± 0.6	μA
Δl _{OFF}	Delta Power Down Leakage Current	$V_1 \text{ or } V_0 = 0V \text{ to } 3.6V$	0V to 0.2V	_	± 0.2	_	± 0.6	μA
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	—	0.5	—	0.9	μA
ΔI _{CC}	Additional Supply Current	One Input at V_{CC} –0.6V Other Inputs at V_{CC} or GND	3.3V	—	40	—	50	μA



Electrical Characteristics (continued)

Symbol	Parameter	Test Conditions	Vcc	T _A = -40°C	to +125°C	Unit
Symbol	Faranieter	Test conditions	VCC	Min	Max	Onic
		_	0.8V to 1.65V	0.80 X V _{CC}		
VIH	High-Level Input Voltage	_	1.65V to 1.95V	0.70 X V _{CC}	_	V
VIH		—	2.3V to 2.7V	1.6	—	v
		—	3.0V to 3.6V	2.0		
			0.8V to 1.65V		0.25 X V_{CC}	
VIL	Low-Level Input Voltage	—	1.65V to 1.95V		0.30 X V _{CC}	V
۷IL			2.3V to 2.7V		0.7	•
			3.0V to 3.6V		0.9	
		I _{OH} = -20μA	0.8V to 3.6V	V _{CC} – 0.11	—	
		I _{OH} = -1.1mA	1.1V	0.6 X V _{CC}	—	
		I _{OH} = -1.7mA	1.4V	0.93	—	
Voh I	High-Level Output Voltage	I _{OH} = -1.9mA	1.65V	1.17	_	V
VOH		I _{OH} = -2.3mA	2.3V	1.77	_	V
		I _{OH} = -3.1mA	2.3V	1.67	—	
		I _{OH} = -2.7mA		2.40	—	
		I _{OH} = -4mA	3V	2.30	—	
		I _{OL} = 20μA	0.8V to 3.6V	_	0.11	
		I _{OL} = 1.1mA	1.1V	_	0.33 X V _{CC}	
		I _{OL} = 1.7mA	1.4V	_	0.41	
.,		I _{OL} = 1.9mA	1.65V	_	0.39	
V _{OL}	Low-Level Input Voltage	I _{OL} = 2.3mA	0.01/	_	0.36	V
		I _{OL} = 3.1mA	2.3V	_	0.50	
		I _{OL} = 2.7mA	0.4		0.36	
		I _{OL} = 4mA	3V	_	0.50	
lı	Input Current	A or B Input, $V_I = GND$ to 3.6V	0V to 3.6V	_	± 0.75	μA
IOFF	Power Down Leakage Current	V_1 or $V_0 = 0V$ to 3.6V	0V		± 1.0	μA
Δl _{OFF}	Delta Power Down Leakage Current	V_1 or V_0 = 0V to 3.6V	0V to 0.2V	_	± 2.5	μA
Icc	Supply Current	$V_{I} = GND \text{ or } V_{CC}, I_{O} = 0$	0.8V to 3.6V	_	3.0	μA
Δlcc	Additional Supply Current	Input at V _{CC} –0.6V Other Inputs at V _{CC} or GND	3.3V	_	75	μA

Operating and Package Characteristics (@T_A = +25°C, unless otherwise specified.)

	Parameter	Tes Condit		Vcc	Тур	Unit	
				0.8V	5.1		
				1.2V ± 0.1V	5.2		
0	Power Dissipation	f = 1N	ЛНz	1.5V ± 0.1V	5.2		
C_{pd}	Capacitance	No Lo	oad	1.8V ± 0.15V	5.5	pF	
				2.5V ± 0.2V	5.7		
				3.3V ± 0.3V	6.0		
Ci	Input Capacitance	$V_i = V_{CC}$	or GND	0V or 3.3V	2.0	pF	
θ_{JA}	Thermal Resistance Junction-to-Ambient	X2-DFN1210-8	(Note 9)	—	+395	°C/W	
θ_{JC}	Thermal Resistance Junction-to-Case	X2-DFN1210-8	(Note 9)	—	+236	°C/W	

Note: 9. Test condition, X2-DFN1210-8 device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



Switching Characteristics

C_L = 5pF, See Figure 1

Parameter	From	То	N	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Input	Output	V _{cc}	Min	Тур	Max	Min	Max	Min	Max	onne	
		0.8V	_	19.6	_	_	_	_	_		
			1.2V ± 0.1V	2.5	5.1	11.9	2.1	13.3	2.1	14.7	ns ns
	A or D	v	1.5V ± 0.1V	1.6	3.7	6.7	1.4	7.8	1.4	8.6	
t _{pd}	A or B	Ŷ	1.8V ± 0.15V	1.3	3.0	5.3	1.1	6.2	1.1	6.9	
			2.5V ± 0.2V	1.0	2.4	3.9	0.9	4.6	0.9	5.1	
			3.3V ± 0.3V	1.0	2.2	3.4	0.8	4.0	0.8	4.4	

C_L = 10pF, See Figure 1

Parameter	From	To Output	V _{cc}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C	Unit	
In In	Input		VCC	Min	Тур	Max	Min	Max	Min	Max	Onit
		0.8V	_	23.5	_	_	—	_	_		
			1.2V ± 0.1V	2.4	6.0	14.1	2.2	15.7	2.2	17.4	- ns
	A or B	v	1.5V ± 0.1V	1.9	4.3	7.9	1.7	9.2	1.7	10.2	
t _{pd}	AUID	T	1.8V ± 0.15V	1.6	3.6	6.2	1.5	7.3	1.5	8.1	
			2.5V ± 0.2V	1.4	3.0	4.7	1.2	5.6	1.2	6.2	
			3.3V ± 0.3V	1.3	2.7	4.2	1.2	5.0	1.2	5.5	

C_L = 15pF, See Figure 1

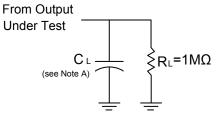
Parameter From		То	V _{cc}	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C to +125°C		Unit
Farameter	Input	Output	VCC	Min	Тур	Max	Min	Max	Min	Max	Onit
			0.8V	_	27.5	_	_	_	_	_	
		1.2V ± 0.1V	3.4	6.8	16.1	3.1	20.2	3.1	20.4		
	A or B	v	1.5V ± 0.1V	2.3	4.8	8.9	2.0	10.4	2.0	11.5	- ns
t _{pd}	AUB	Ť	1.8V ± 0.15V	1.9	4.0	7.0	1.7	8.3	1.7	9.2	
			2.5V ± 0.2V	1.7	3.4	5.4	1.5	6.3	1.5	7.0	
			3.3V ± 0.3V	1.4	3.2	4.8	1.3	5.7	1.3	6.3	

C_L = 30pF, See Figure 1

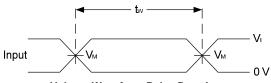
Parameter	From	To Output	Vcc	T _A = +25°C			T _A = -40°C to +85°C		T _A = -40°C	Unit	
Farameter	Input		VCC	Min	Тур	Max	Min	Max	Min	Max	Unit
		0.8V	_	39.3	_	_	_	_	_		
			1.2V ± 0.1V	4.6	9.0	21.9	4.1	27.6	4.1	27.8	
	A or B	v	1.5V ± 0.1V	3.4	6.4	11.8	2.9	13.9	2.9	15.3	
t _{pd}	AUID	T	1.8V ± 0.15V	2.6	5.3	9.3	2.3	11.1	2.3	12.3	ns
			2.5V ± 0.2V	2.4	4.5	7.1	2.1	8.5	2.1	9.4	
			3.3V ± 0.3V	2.0	4.2	6.4	1.8	7.7	1.8	8.5	



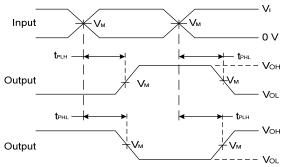
Parameter Measurement Information



Vcc	Inputs		, v	•
	VI	t _r /t _f	V _M	C∟
0.8V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.2V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.5V ± 0.1V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
1.8V ± 0.15V	Vcc	≤3ns	V _{CC} /2	5, 10, 15, 30pF
2.5V ± 0.2V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF
3.3V ± 0.3V	V _{CC}	≤3ns	V _{CC} /2	5, 10, 15, 30pF







Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. All pulses are supplied a pulse repetition rate ≤ 10 MHz.
 C. Inputs are measured separately one transition per measurement.

D. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$



Marking Information

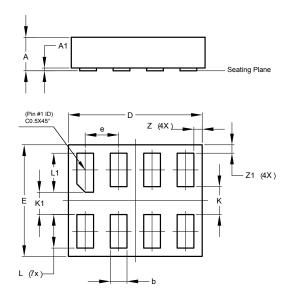
X2-DFN1210-8

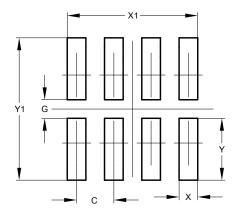


Part Number	Package	Identification Code	
74AUP2G02RA3-7	X2-DFN1210-8	BT	

X2-DFN1210-8 Package Outline Dimensions and Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.





X2-DFN1210-8				
Dim	Min	Max	Тур	
Α	-	0.35	0.30	
A1	0	0.03	0.02	
b	0.10	0.20	0.15	
D	1.15	1.25	1.20	
Е	0.95	1.05	1.00	
е	-	-	0.30	
К	-	-	0.25	
K1	-	-	0.20	
L	0.25	0.35	0.30	
L1	0.30	0.40	0.35	
Z	0.050	0.100	0.075	
Z1	0.050	0.100	0.075	
All Dimensions in mm				

Dimensions	Value (in mm)	
С	0.300	
G	0.150	
Х	0.150	
X1	1.050	
Y	0.500	
Y1	1.150	



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